NSN 5961-01-252-6944

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View Online at https://aerobasegroup.com/nsn/5961-01-252-6944 **Inclosure Material:** Glass and metal **Overall Length:** 0.175 inches **Terminal Length:** 1.500 inches **Overall Diameter:** 0.370 inches **Internal Configuration:** Junction contact Joint Electronic Device Engineering Council/jedec/case Outline Designation: To-5 **Response Time:** 5.0 microseconds **Mounting Method: Terminal Terminal Circle Diameter:** 0.300 inches **Features Provided:** Hermetically sealed case **Semiconductor Material:** Silicon **Voltage Rating In Volts Per Characteristic:** 250.0 regulator voltage **Current Rating Per Characteristic:** 75.00 amperes repetitive peak forward current peak **Power Rating Per Characteristic:** 2.2 watts small-signal input power, common-emitter blank **Special Features:** Junction pattern arrangement: pn **Precious Material And Location:** Terminal surfaces gold **Precious Material:** Gold **Terminal Type And Quantity:** 3 uninsulated wire lead Shelf Life: N/a **Unit Of Measure:**

Demilitarization:

Yes - demil/mli

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